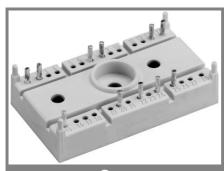
SK 40 DT



SEMITOP® 3

Controllable Bridge Rectifier

SK 40 DT

Preliminary Data

Features

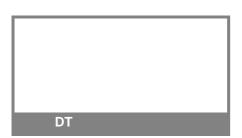
- Compact design
- · One screw mounting
- Heat transfer and insolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

Typical Applications

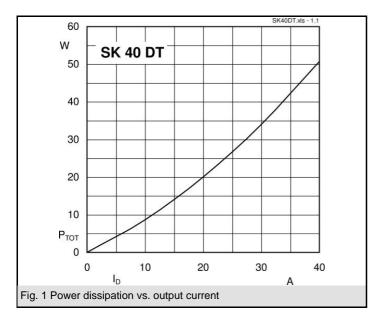
- Soft starters
- Light control
- · Temperature control
- Motor control

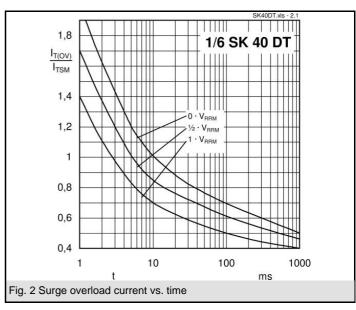
V _{RSM}	V _{RRM} , V _{DRM}	I _D = 42 A (full conduction)
900	800	(T _s = 80 °C) SK 40 DT 08
1300	1200	SK 40 DT 12
1700	1600	SK 40 DT 16

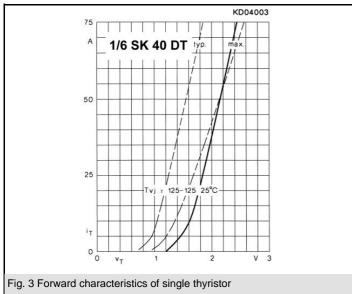
Symbol	Conditions	Values	Units
I _D	T _s = 80 °C	42	Α
I _{FSM}	T _{vi} = 25 °C; 10 ms	320	Α
	T _{vj} = 125 °C; 10 ms	280	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	510	A²s
	T _{vj} = 125 °C; 8,310 ms	390	A²s
V_T	T _{vj} = 25 °C; 75A	max. 2,45	V
$V_{T(TO)}$	T _{vj} = 125 °C;	1,1	V
r _T	$T_{vj} = 125 ^{\circ}\text{C}$	20	$m\Omega$
$I_{DD}; I_{RD}$	T_{vj} = 125 °C; V_{DD} = V_{DRM} ; V_{RD} = V_{RRM}	max. 8	mA
t_{gd}	$T_{vj} = {^{\circ}C}; I_G = A; di_G/dt = A/\mu s$		μs
t _{gr}	$V_D = \cdot V_{DRM}$		μs
(dv/dt) _{cr}	T _{vj} = 125 °C; d.c.	max. 1000	V/µs
(di/dt) _{cr}	$T_{vi} = 125 ^{\circ}\text{C}; \text{d.c.}; \text{f} = 5060 \text{Hz}$	max. 100	A/µs
t _q	T_{vj}^{3} = 125 °C; d.c.; typ.	80	μs
I _H	T_{vj} = 25 °C; d.c.; typ. / max.	80 / 150	mA
IL	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}; R_{G} = 33 \Omega$	150 / 300	mA
V _{GT}	T _{vj} = 25 °C; d.c.	min. 2	V
I _{GT}	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 100	mA
V_{GD}	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
I_{GD}	T _{vj} = 125 °C; d.c.	max. 3	mA
Rth(j-s)	Per thyristor	1,7	K/W
			K/W
T _{solder}	Terminals, 10s	260	°C
T _{vi}		-40+125	°C
T _{stg}		-40+125	°C
V _{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 (2500)	V
M _s	Mounting torque to heatsink	2,5	Nm
а			m/s²
m	weight	30	g
Case	SEMITOP® 3	T 15	

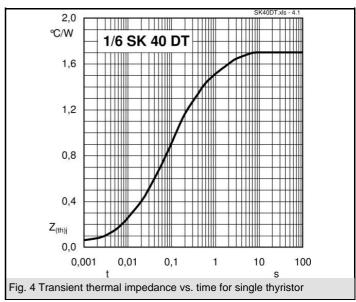


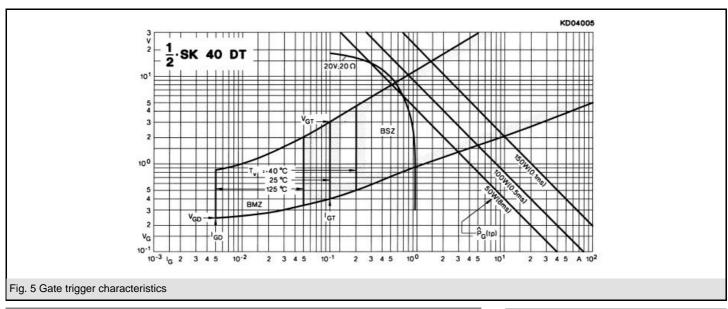
SK 40 DT

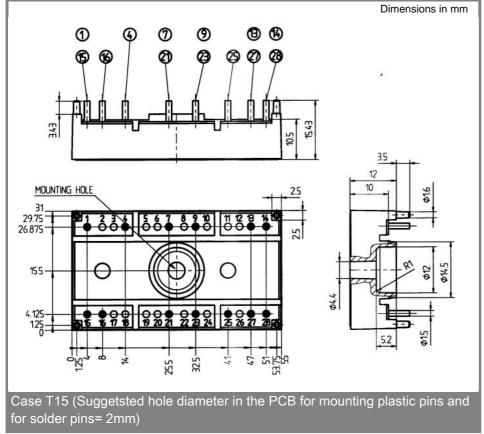


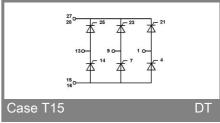












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